

C4D20120A

Silicon Carbide Schottky Diode

Z-REC[®] RECTIFIER

V_{RRM}	=	1200 V
$I_F (T_C=135^{\circ}\text{C})$	=	25.5 A
Q_c	=	99 nC

Features

- 1.2kV Schottky Rectifier
- Zero Reverse Recovery Current
- High-Frequency Operation
- Temperature-Independent Switching
- Extremely Fast Switching

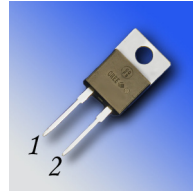
Benefits

- Replace Bipolar with Unipolar Rectifiers
- Essentially No Switching Losses
- Higher Efficiency
- Reduction of Heat Sink Requirements
- Parallel Devices Without Thermal Runaway

Applications

- Switch Mode Power Supplies
- Power Factor Correction
- Motor Drives

Package



TO-220-2



Part Number	Package	Marking
C4D20120A	TO-220-2	C4D20120

Maximum Ratings ($T_C=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
V_{RRM}	Repetitive Peak Reverse Voltage	1200	V		
V_{RSM}	Surge Peak Reverse Voltage	1300	V		
V_R	DC Peak Reverse Voltage	1200	V		
I_F	Continuous Forward Current	53.5 25.5 20	A	$T_C=25^{\circ}\text{C}$ $T_C=135^{\circ}\text{C}$ $T_C=150^{\circ}\text{C}$	
I_{FRM}	Repetitive Peak Forward Surge Current	91 61	A	$T_C=25^{\circ}\text{C}$, $t_p=10$ ms, Half Sine Pulse $T_C=110^{\circ}\text{C}$, $t_p=10$ ms, Half Sine Pulse	
I_{FSM}	Non-Repetitive Forward Surge Current	130 110	A	$T_C=25^{\circ}\text{C}$, $t_p=10$ ms, Half Sine Pulse $T_C=110^{\circ}\text{C}$, $t_p=10$ ms, Half Sine Pulse	
$I_{F,Max}$	Non-Repetitive Peak Forward Current	1150 950	A	$T_C=25^{\circ}\text{C}$, $t_p=10$ μs , Pulse $T_C=110^{\circ}\text{C}$, $t_p=10$ μs , Pulse	
P_{tot}	Power Dissipation	242 104	W	$T_C=25^{\circ}\text{C}$ $T_C=110^{\circ}\text{C}$	
T_J	Operating Junction Range	-55 to +175	$^{\circ}\text{C}$		
T_{stg}	Storage Temperature Range	-55 to +135	$^{\circ}\text{C}$		
	TO-220 Mounting Torque	1 8.8	Nm lbf-in	M3 Screw 6-32 Screw	

Electrical Characteristics

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
V_F	Forward Voltage	1.5 2.2	1.8 3	V	$I_F = 20\text{ A}$ $T_J = 25^\circ\text{C}$ $I_F = 20\text{ A}$ $T_J = 175^\circ\text{C}$	
I_R	Reverse Current	35 65	200 400	μA	$V_R = 1200\text{ V}$ $T_J = 25^\circ\text{C}$ $V_R = 1200\text{ V}$ $T_J = 175^\circ\text{C}$	
Q_C	Total Capacitive Charge	99		nC	$V_R = 800\text{ V}$, $I_F = 20\text{ A}$ $di/dt = 200\text{ A}/\mu\text{s}$ $T_J = 25^\circ\text{C}$	
C	Total Capacitance	1500 93 67		pF	$V_R = 0\text{ V}$, $T_J = 25^\circ\text{C}$, $f = 1\text{ MHz}$ $V_R = 400\text{ V}$, $T_J = 25^\circ\text{C}$, $f = 1\text{ MHz}$ $V_R = 800\text{ V}$, $T_J = 25^\circ\text{C}$, $f = 1\text{ MHz}$	

Note:

1. This is a majority carrier diode, so there is no reverse recovery charge.

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
$R_{\theta JC}$	Thermal Resistance from Junction to Case	0.62		$^\circ\text{C}/\text{W}$		

Typical Performance

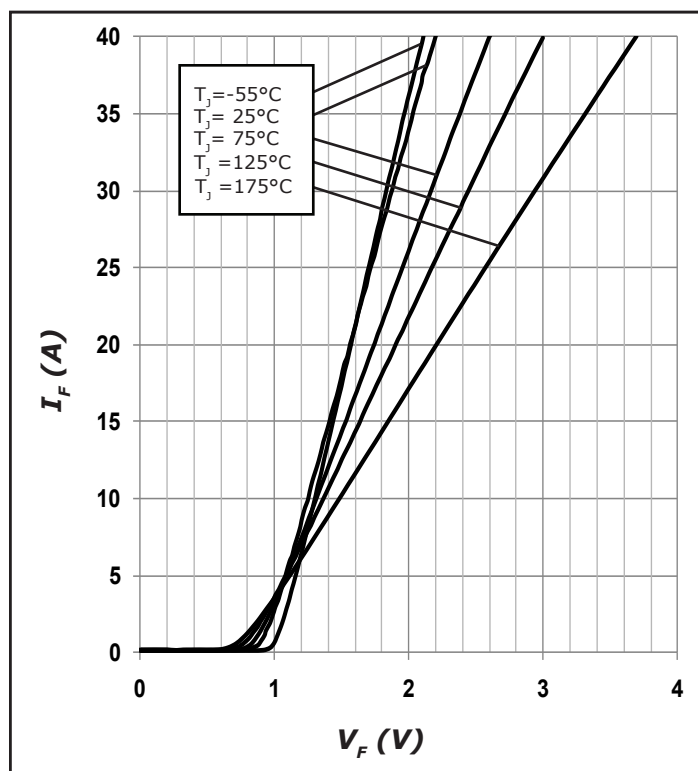


Figure 1. Forward Characteristics

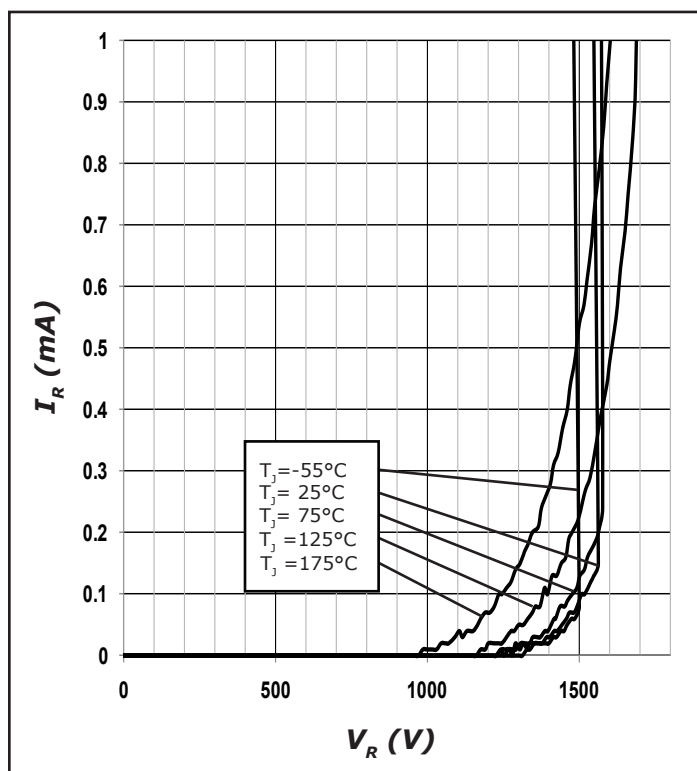


Figure 2. Reverse Characteristics

Typical Performance

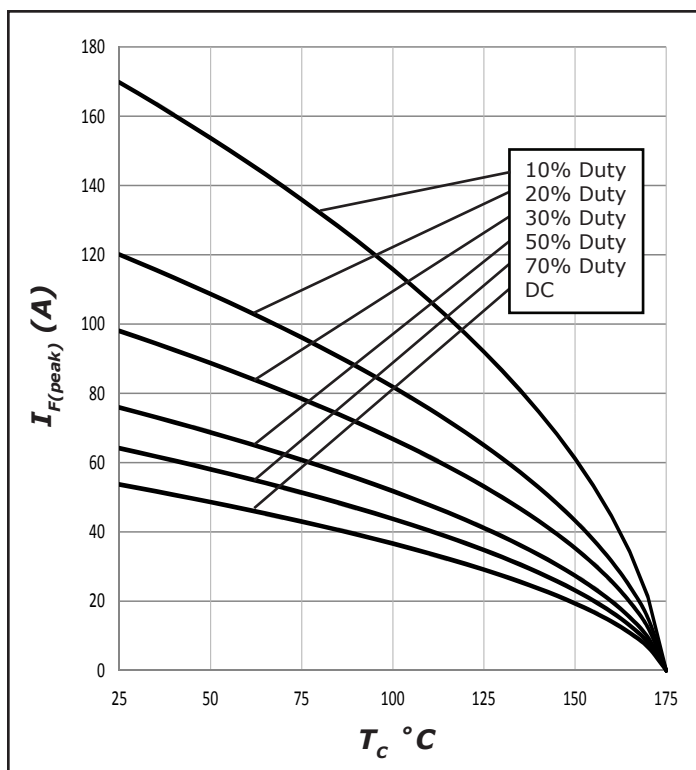


Figure 3. Current Derating

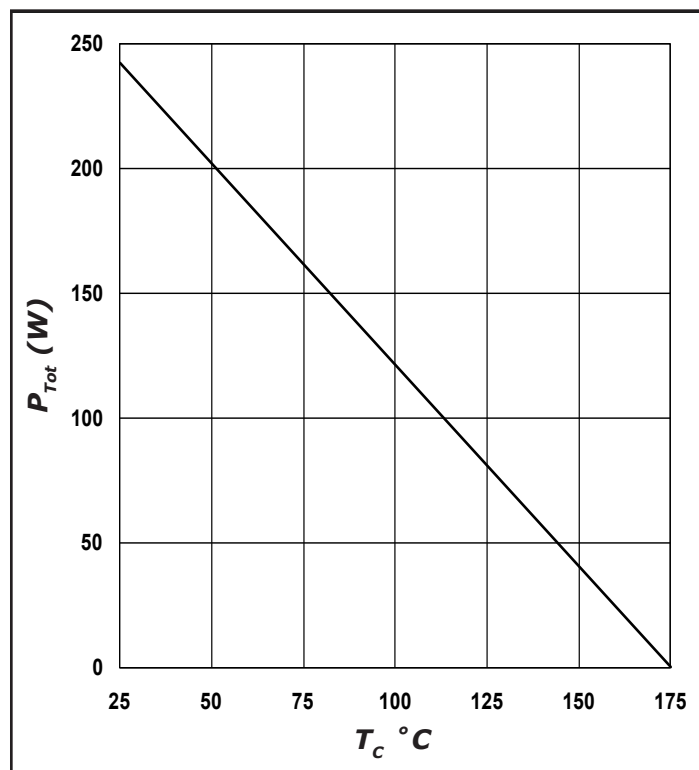


Figure 4. Power Derating

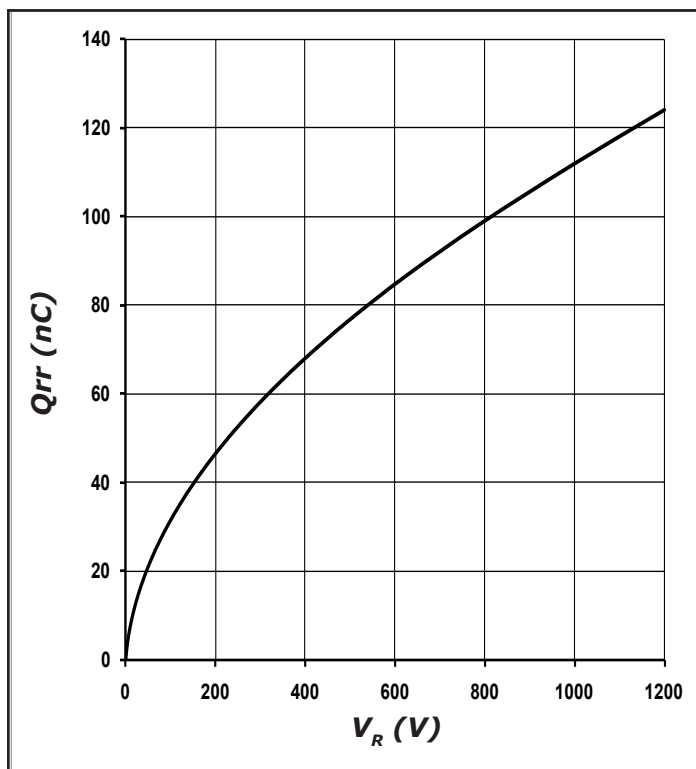


Figure 5. Recovery Charge vs. Reverse Voltage

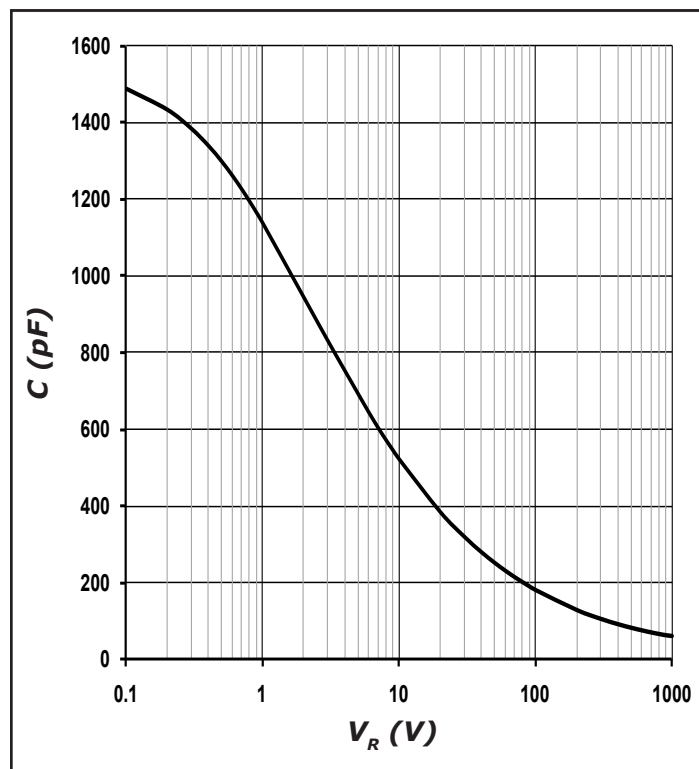


Figure 6. Capacitance vs. Reverse Voltage

Typical Performance

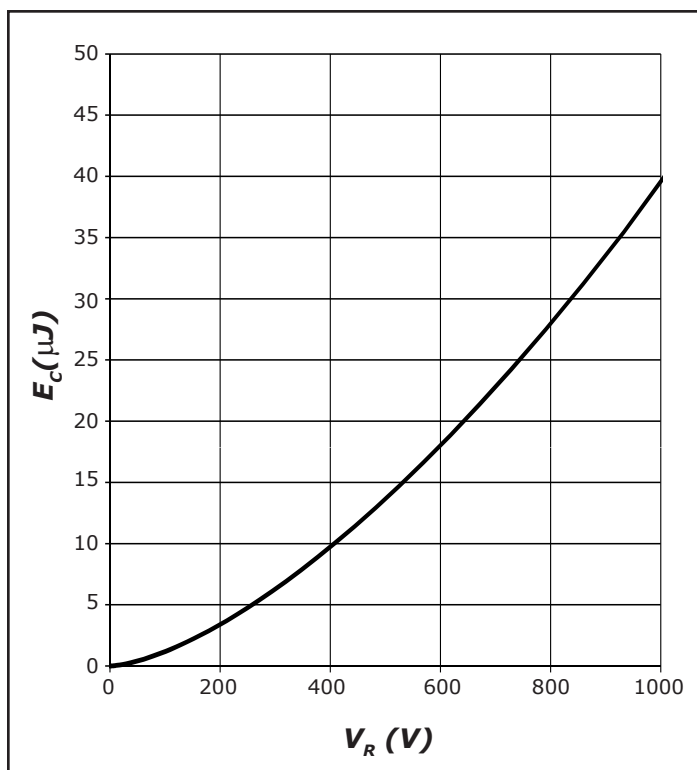


Figure 7. Typical Capacitance Stored Energy

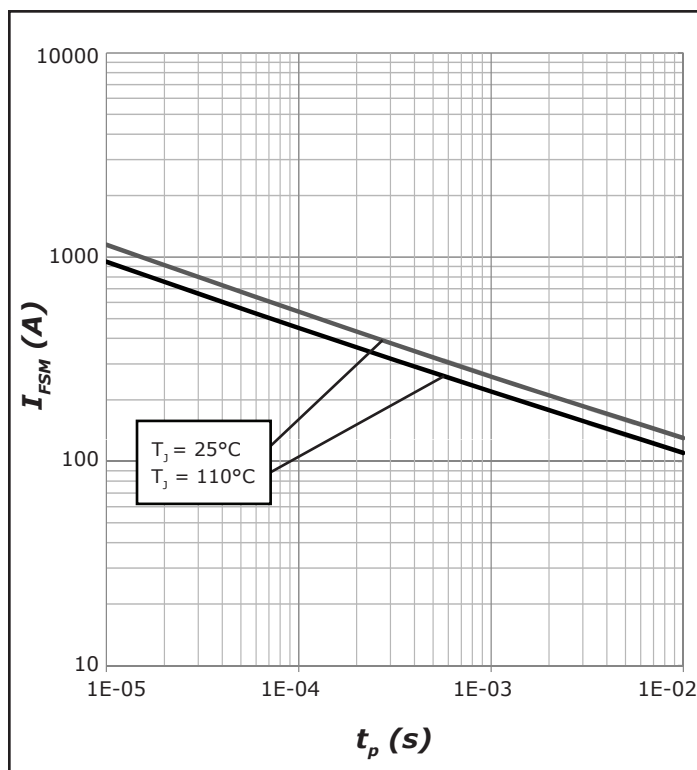


Figure 8. Non-Repetitive Peak Forward Surge Current versus Pulse Duration (sinusoidal waveform)

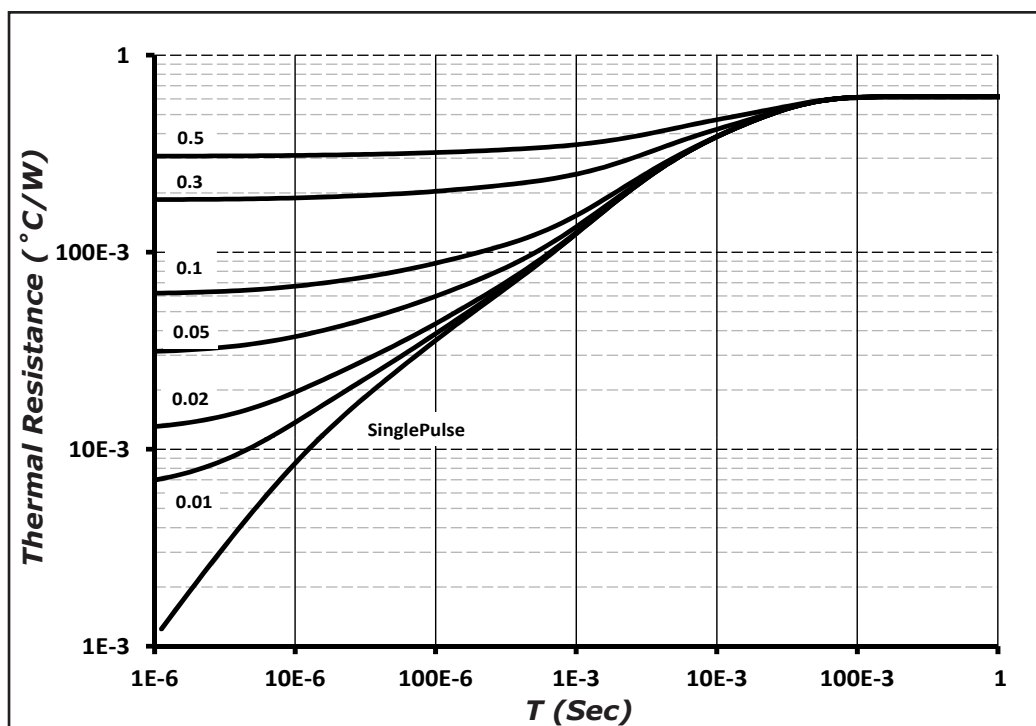
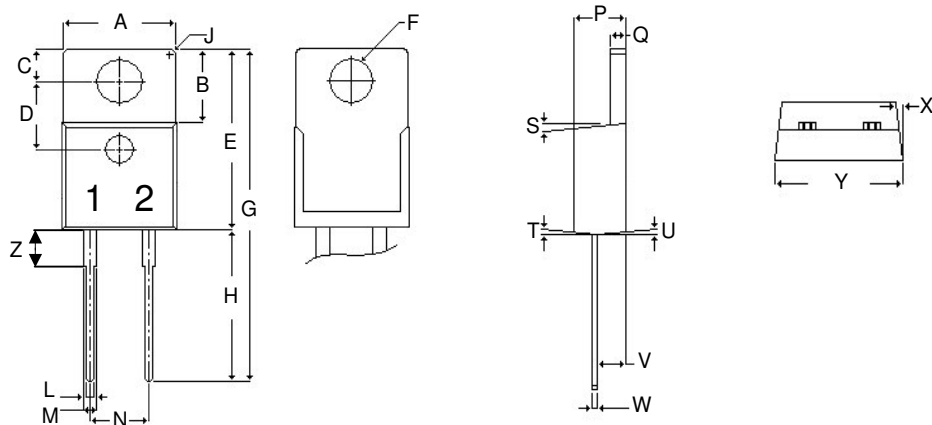


Figure 9. Transient Thermal Impedance

Package Dimensions

Package TO-220-2

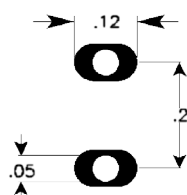


POS	Inches		Millimeters	
	Min	Max	Min	Max
A	.381	.410	9.677	10.414
B	.235	.255	5.969	6.477
C	.100	.120	2.540	3.048
D	.223	.337	5.664	8.560
E	.590	.615	14.986	15.621
F	.143	.153	3.632	3.886
G	1.105	1.147	28.067	29.134
H	.500	.550	12.700	13.970
J	R 0.197		R 0.197	
L	.025	.036	.635	.914
M	.045	.055	1.143	1.397
N	.195	.205	4.953	5.207
P	.165	.185	4.191	4.699
Q	.048	.054	1.219	1.372
S	3°	6°	3°	6°
T	3°	6°	3°	6°
U	3°	6°	3°	6°
V	.094	.110	2.388	2.794
W	.014	.025	.356	.635
X	3°	5.5°	3°	5.5°
Y	.385	.410	9.779	10.414
z	.130	.150	3.302	3.810

NOTE:

1. Dimension L, M, W apply for Solder Dip Finish

Recommended Solder Pad Layout



TO-220-2

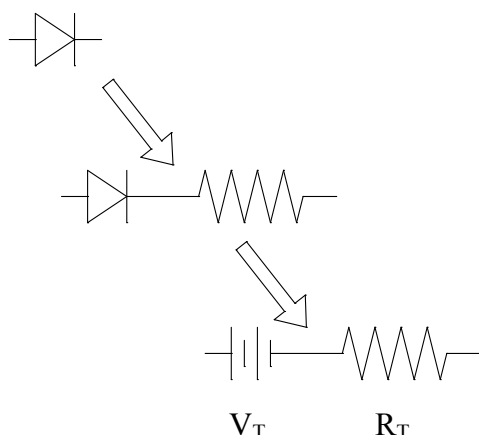
Part Number	Package	Marking
C4D20120A	TO-220-2	C4D20120

Note: Recommended soldering profiles can be found in the applications note here:

http://www.cree.com/power_app_notes/soldering



Diode Model



$$V_{fT} = V_T + I_f \cdot R_T$$

$$V_T = 0.97 + (T_j \cdot -1.40 \cdot 10^{-3})$$

$$R_T = 0.023 + (T_j \cdot 2.71 \cdot 10^{-4})$$

Note: T_j = Diode Junction Temperature In Degrees Celsius,
valid from 25°C to 175°C

Notes

- RoHS Compliance**

The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC (RoHS2), as implemented January 2, 2013. RoHS Declarations for this product can be obtained from your Cree representative or from the Product Documentation sections of www.cree.com.

- REACH Compliance**

REACH substances of high concern (SVHCs) information is available for this product. Since the European Chemical Agency (ECHA) has published notice of their intent to frequently revise the SVHC listing for the foreseeable future, please contact a Cree representative to insure you get the most up-to-date REACH SVHC Declaration. REACH banned substance information (REACH Article 67) is also available upon request.

- This product has not been designed or tested for use in, and is not intended for use in, applications implanted into the human body nor in applications in which failure of the product could lead to death, personal injury or property damage, including but not limited to equipment used in the operation of nuclear facilities, life-support machines, cardiac defibrillators or similar emergency medical equipment, aircraft navigation or communication or control systems, or air traffic control systems.